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6447604, 6440323, and 6156581. I am a co-inventor of the subject matter of the above-referenced patent application.

2. The claims of the above-referenced patent application (for example, claim 1) recite large area of at least 15 cm^2 and low dislocation density not exceeding 3×10^6 dislocations per cm^2 of growth surface area on the face.

3. I understand that all of the claims of the above-referenced patent application have been rejected. I have reviewed the Final Office Action dated February 17, 2007 and the Office Action dated July 26, 2006 (collectively, "the Office Actions"), along with U.S. Patent No. 6,806,508 to D'Evelyn (hereinafter, "D'Evelyn '508") relied upon by the Examiner in the rejection of the claims. I have further reviewed a paper by M.P. D'Evelyn et al. entitled "Growth and Characterization of Bulk GaN Crystals at High Pressure and High Temperature" (Mat. Res. Soc. Symp. Proc. Vol. 798, Materials Research Society, 2004) (hereinafter, the "D'Evelyn Paper") (attached as Exhibit A). Based on my review of these documents, I have the following comments relating to the Office Actions.

4. D'Evelyn '508 contemplates "single gallium nitride crystals having a diameter and a thickness in a range from about 0.02 inch (about 0.05 cm) to about 12 inches (about 30 cm) and, for example, a size in a range from about 2 inches to about 6 inches" (D'Evelyn '508, col. 4, lines 61-66). This is an extremely wide range, i.e., representing a 600-fold span from the lowest value (e.g., 0.02 inch) to the highest value (e.g., 12 inches).

5. D'Evelyn '508 purports to teach the fabrication of large area gallium nitride crystals via a "high pressure high temperature" process, with the following excerpt from D'Evelyn '508 representing the most detailed instructions for implementing such grown process:

More specifically, one suitable process for forming the GaN substrate comprises providing a source gallium nitride, solvent, and mineralizer. The source gallium nitride may comprise at least one of poorly-crystallized gallium nitride, well-crystallized gallium nitride, amorphous gallium nitride, polycrystalline gallium nitride, and combinations thereof. The source gallium nitride may be provided "as-is" in its raw form. Alternatively, the source gallium nitride can be compacted into a "pill" or sintered into a polycrystalline compact. Alternatively, the source gallium nitride can be formed in situ by providing gallium metal which then reacts with the ammonia solvent after sealing of the capsule and treatment at high pressure and high temperature to form source gallium nitride.

The source gallium nitride may then be combined with at least one of the mineralizer and solvent to form a mixture. The gallium nitride, solvent, and mineralizer may optionally be provided individually to the capsule as separate and distinct un-combined materials. The mixture, which can comprise gallium

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nitride and at least one of the solvent and mineralizer, can be optionally compacted into a pill, however the compacting of the mixture need not be conducted in the gallium nitride growth process.

The source gallium nitride, solvent, and mineralizer are then placed inside a capsule as either a compacted or uncompact mixture. Optionally, additional mineralizer can also be added to the capsule. The capsule, which will be described hereinafter, can then be filled with a nitrogen-containing solvent, for example at least one of ammonia or hydrazine, or an organic solvent, including but not limited to, methylamine, melamine, ethylene diamine, and mixtures thereof. The capsule is then sealed, disposed in a pressure cell, and subjected to high pressure and high temperature conditions in an appropriate high pressure high temperature (HPHT) system. The HPHT conditions are maintained for a length of time sufficient to dissolve the source gallium nitride and re-precipitate it onto at least one gallium nitride crystal, gallium nitride boule, or gallium nitride crystal seed.

Maintaining HPHT conditions yields large single gallium nitride crystals, for example single gallium nitride crystals having a diameter and thickness in a range from about 0.02 inch (about 0.05 cm) to about 12 inches (about 30 cm) and, for example, a size in a range from about 2 inches to about 6 inches. The pressure, as embodied by the invention, is in a range from greater than about 5 kbar to about 80 kbar, and the temperature for the gallium nitride crystal growth process is in a range between about 550.degree. C. and about 3000.degree. C. The GaN single crystals thus formed are substantially transparent, with an absorption coefficient below 100 cm.sup.-1. Furthermore, the substrates of the present invention have carrier mobilities above about 100 cm.sup.2 /V-s and strain, with respect to undoped GaN homoepitaxial layers, below about 0.005%.

D'Evelyn '508, col. 4, line 22 – col. 5, line 8 (annotated).

6. While D'Evelyn '508 purports to teach the fabrication of large area gallium nitride crystals and to further teach the fabrication of low defect density gallium nitride crystals, the disclosure of D'Evelyn '508 gives rise to many critical but unanswered questions regarding fabrication of gallium nitride crystals characterized simultaneously by both large area and low defect density. Such questions include:

- (A) How is growth nucleated to replicate the seed and prevent inhomogeneity and cracking in the growing GaN crystal according to D'Evelyn's HPHT process?
- (B) How are spurious deposits eliminated so that high quality growth can be carried out for the presumably many days and/or weeks needed to make large area crystals according to D'Evelyn's HPHT process?

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- (C) What measures are taken to eliminate the nucleation of polycrystalline growth or evolving growth conditions with growth of a large crystal according to D'Evelyn's HPHT process?
- (D) How are during growth stresses managed to eliminate cracking, which would reduce the useful size of the resulting crystal grown according to D'Evelyn's HPHT process?

Answers to the foregoing questions (A)-(D) would be necessary for one of ordinary skill in the art to grow GaN crystals characterized simultaneously by large area and low defect density (i.e., within the scope of the claims of the present U.S. Patent Application No. 10/712,351) using the high pressure high temperature process of D'Evelyn '508. Nothing in D'Evelyn '508 provides any answers or guidance relating to any of the foregoing questions (A)-(D).

7. These gaps in the disclosure of D'Evelyn '508, together with my understanding of the level of ordinary skill in the art at the time U.S. Patent Application No. 09/839,941 (that matured into D'Evelyn '508) was filed, support my conclusion that D'Evelyn '508 fails to enable large area, low defect density GaN within the scope of the claims of the present U.S. Patent Application No. 10/712,351.

8. Generally speaking, at the time the present invention was made, it was not difficult for one skilled in the art to grow low dislocation density GaN crystals of small size, but it was many magnitudes more difficult to grow GaN crystals characterized by BOTH large area and low dislocation density.

9. D'Evelyn '508 specifically avoids any recitation of dislocation density achieved by the so-called 'high pressure high temperature' or "HPHT" process as applied to a GaN crystal of any particular size. Likewise, D'Evelyn '508 fails to claim low dislocation density GaN in conjunction with a crystal of any particular size.

10. D'Evelyn '508 includes claims directed solely to photodetectors, to the exclusion of any claims directed to large area, low dislocation density GaN crystals. One skilled in the art would instantly recognize that the value of patent cover for large area, low dislocation density GaN crystals (which are susceptible to a variety of uses) would be many times greater than the relatively narrow photodetector claims provided in D'Evelyn '508. The failure of D'Evelyn '508 to claim large area, low dislocation density GaN is consistent with D'Evelyn's failure to enable such subject matter.

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11. In the D'Evelyn Paper, Mr. D'Evelyn (along with the other authors) admits that "[t]he largest [GaN] crystal we have grown to date is 15x18 mm in diameter" using a purported high temperature high pressure process. See D'Evelyn Paper at page 276, bottom paragraph. Moreover, in the final passage, D'Evelyn and his co-authors state their belief "that continued development of the present method will permit low-cost manufacturing of high-quality true bulk GaN boules and wafers larger than 50 mm in diameter." (Emphasis added.) The D'Evelyn Paper was published in 2004 – three years after the filing in 2001 of U.S. patent application 09/839,941 that matured into D'Evelyn '508. If Mr. D'Evelyn (as co-inventor of D'Evelyn '508) had truly enabled GaN crystals of up to 12 inch diameter in 2001 using a high pressure high temperature process, it is bewildering – to say the least – that after three years of additional research, he was unable to produce single crystals of GaN greater than 18 mm (i.e., under 1 inch) diameter in 2004, again using a high pressure high temperature process. Likewise, if Mr. D'Evelyn had enabled 12 inch diameter GaN crystals in 2001, why would "continued development" be necessary in 2004 to support scalability of the high pressure high temperature process to produce GaN wafers larger than 50 mm (2.3 inches)? These facts further support my conclusion that D'Evelyn '508 failed to enable the fabrication of large area, low defect density GaN within the scope of the claims of the present U.S. Patent Application No. 10/712,351.

12. Moreover, close examination of the D'Evelyn Paper reveals that the authors again took great care to list size and defect (e.g., dislocation) density characteristics of GaN crystals separately so that dislocations and area are not necessarily provided together for any single wafer. A hundred-fold (two order of magnitude) range of defect density, i.e., 10^6 to 10^8 cm^{-2} , was reported for etch pit density in the D'Evelyn Paper (with such a wide range suggesting process inconsistency), but without specific correlation of defect density to any particular wafers. Notably, the largest area wafer (D'Evelyn Paper, page 277, Fig. 4) was "dark" in appearance, which appearance is not consistent with low dislocation density. To the contrary, low defect density GaN should be clear or translucent in appearance. These facts further support my conclusion that Mr. D'Evelyn failed to enable or demonstrate possession of a method for producing large area, low defect density GaN (i.e., within the scope of the claims of the present U.S. Patent Application No. 10/712,351) at the time of filing of U.S. Patent Application No. 09/839,941, which matured into D'Evelyn '508.

13. Based on the foregoing, there exists no basis for the Examiner's conclusion that D'Evelyn '508 enables the claims of the present patent application

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I declare under penalty of perjury that the facts set forth in this declaration are true and correct, that all statements made of my own knowledge are true, and that all statements made on information and belief are believed to be true. I have been hereby warned that willful false statements and the like so made are punishable by fine or imprisonment, or both, under 18 U.S.C. § 1001, and that such willful false statements may jeopardize the validity of the application or any resulting registration.

Executed at Durham, North Carolina, this 12th day of April 2007.


Robert P. Vaudo

EXHIBIT A

Growth and Characterization of Bulk GaN Crystals at High Pressure and High Temperature

M. P. D'Evelyn^a, K. J. Narang^a, D.-S. Park^a, H. C. Hong^a, M. Barbe^a, S. A. Tysoe^a, J. Leman^b, J. Balch^a, V. L. Lou^a, S. F. LeBocuf^a, Y. Gao^a, J. A. Tectsov^a, P. J. Codella^a, P. R. Tavcner^b, D. R. Clarke^b, and R. J. Molnar^c

^a GE Global Research Center, Niskayuna, NY 12309 USA

^b Materials Department, College of Engineering, University of California at Santa Barbara, Santa Barbara, CA 93106-5050 USA

^c Massachusetts Institute of Technology, Lincoln Laboratory, Lexington, MA 02173-9108 USA

ABSTRACT

We report the growth and characterization of bulk GaN single crystals by temperature-gradient recrystallization at high pressure and high temperature (HPHT), using apparatus adapted from that used to synthesize gem-grade diamond crystals. The bulk crystals are grown on seeds that were synthesized by hydride vapor phase epitaxy (HVPE) and subsequently removed from their sapphire substrate. Our largest crystals to date are 15×18 mm in diameter; however, the process is scalable to 50 mm and above. The crystals are transparent and well faceted, and dislocation densities below 100 cm⁻² have been achieved. Additional characterization of the GaN crystals is also presented.

INTRODUCTION

Gallium nitride based optoelectronic and electronic device applications have grown spectacularly during the past decade, led by light-emitting diodes (LEDs) and laser diodes. However, the performance and reliability of these devices are compromised by the lack of high quality, cost-effective native substrates. Threading dislocations, with a typical concentration of 10⁹-10¹⁰ cm⁻² in heteroepitaxial GaN layers on sapphire or SiC, decrease the efficiency and maximum intensity of light emission in ultraviolet LEDs [1] and the lifetime of laser diodes [2].

Many laboratories and companies are working on growth of bulk and pseudo-bulk GaN substrates but no fully satisfactory solution is yet at hand. By far the most mature technology is the growth of thick quasi-bulk GaN substrates, typically on sapphire, GaAs, or LiAlO₂, by hydride/halide vapor phase epitaxy, or HVPE [3,4]. HVPE is currently capable of routinely producing free-standing GaN wafers with a dislocation density of about 10⁷ cm⁻², although lower values have been reported over at least restricted regions (e.g., within a grain) [4]. However, as a one- or few-at-a-time growth technique, wafers produced by this method are likely to remain rather expensive. In addition, for a number of device applications, lower dislocation densities may be required. Growth of GaN in liquid Ga under a high N₂ pressure is capable of growing high-quality platelets, approximately 10 nm × 10 nm × 100 μm in dimension with dislocation densities in the range of 10-10⁵ cm⁻² [5]. However, the growth conditions are severe (10-15 kbar pressure), growth rates are rather small, and no one has been able to demonstrate routine growth of larger crystals by this method, despite extensive efforts by several groups [5,6]. Interesting results have also been obtained on growth of GaN in Ga-based alloys under milder pressures [7], but definitive data on the dislocation densities achievable by the latter methods are not yet available.

After silicon, the electronic crystal grown on the largest scale is α -quartz, at the level of thousands of tons per year. Quartz is grown commercially in supercritical water at about 400 °C and 2 kbar in large autoclaves, and if GaN could be grown by an analogous method the cost could be modest. A number of groups have reported growth of GaN in supercritical ammonia [8], but to date the growth rates and crystal quality achieved have been rather modest.

EXPERIMENTAL

In the present work, we have performed GaN growth in supercritical ammonia, but at considerably higher temperatures and pressures than have been accessible to other groups using conventional autoclaves. Single-crystal GaN seeds were grown by HVPE on sapphire substrates to a thickness of about 200 μm , as described elsewhere [3,9]. The sapphire was then removed by laser-liftoff or by conventional lapping with a diamond powder slurry. One or more GaN seeds, polycrystalline GaN raw material, a mineralizer, and ammonia were then sealed into a capsule. The capsule was incorporated into a high-pressure cell capable of producing a temperature gradient, of the type used in diamond synthesis [10], and placed in a press apparatus, as illustrated schematically in Fig. 1. Crystals were grown at temperatures between 600 and 1000 °C at liquid ammonia fills (% of available volume in the capsule) of about 70-95%. Based on an extrapolation of the equation-of-state data [11], the pressure is estimated as lying between about 5 and 20 kbar, as shown by the solid lines in Fig. 2. Partial dissociation of NH_3 into $\frac{1}{2} \text{N}_2 + \frac{3}{2} \text{H}_2$ could increase the pressure, as shown by the dashed lines in Fig. 2, calculated using the known equilibrium constant and assuming ideal gas behavior.

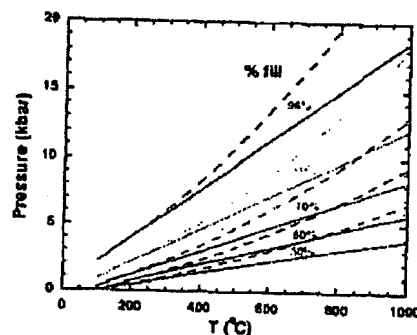
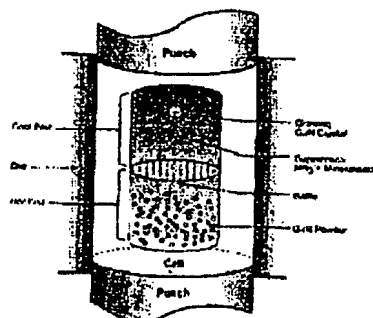


Fig. 1. Schematic of crystal growth apparatus. Fig. 2. Estimated pressure-fill diagram for NH_3 .

RESULTS AND DISCUSSION

GaN crystals grown by our method are transparent and well faceted, with roughly similar growth rates in the c- and ab-directions. An example of mm-sized spontaneously-nucleated crystals is shown in Fig. 3. The largest crystal we have grown to date is 15x18 mm in diameter, as shown in Fig. 4. The non-transparency of this crystal results from the seed. A transparent 10x13 mm crystal, grown on a clear seed, is shown in Fig. 5.

Fig. 3. Spontaneously-nucleated GaN

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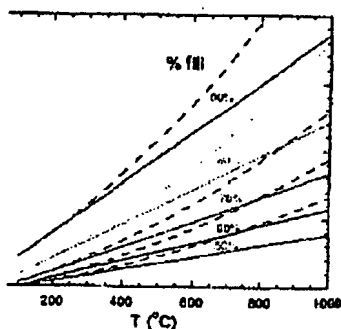
Under a polar hexagonal facets on one ray diffraction measured into to those predicted achieved, with the analysis prismatic GaN surface is

The surface microscopy (6. The RMS may be residual. The N face appears elsewhere AFM. The C reports [12] r

The root mean square, was done geometry will are shown in 530 cm⁻¹; E₁. The selection Particularly peak assignment concentration

largest scale is α -quartz, at the level of ally in supercritical water at about 400 °C own by an analogous method the cost growth of GaN in supercritical ammoniaieved have been rather modest.

with in supercritical ammonia, but at ive been accessible to other groups using re grown by HVPE on sapphire substrates [3,9]. The sapphire was then removed by powder slurry. One or more GaN seeds, monia were then sealed into a capsule, capable of producing a temperature id placed in a press apparatus, as 1 at temperatures between 600 and 1000 e capsule) of about 70-95%. Based on a ssure is estimated as lying between about rial dissociation of NH_3 into $\frac{1}{2} \text{N}_2 + \frac{3}{2} \text{H}_2$ lines in Fig. 2, calculated using the ravior.



Estimated pressure-fill diagram for NH_3 .

: and well faceted, with roughly similar un-sized spontaneously-nucleated, grown to date is 15x18 mm in diameter, results from the seed. A transparent ig. 5.



Fig. 3. Spontaneously-nucleated GaN crystal.

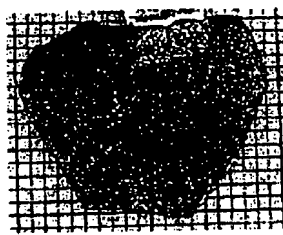


Fig. 4. 15x18 mm crystal grown on a UCSB seed.

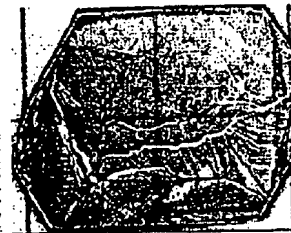


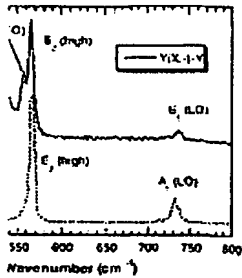
Fig. 5. 10x13 mm crystal grown on an MIT-LL seed.

The crystals are typically yellow in color rather than colorless, which we attribute to oxygen, currently present at levels above 100 ppm. The oxygen originates mainly from oxide in the polycrystalline GaN raw material and from water in the mineralizer, and we expect that it will be possible to greatly reduce its concentration. An experiment with the purest raw materials we have produced to date resulted in a GaN crystal that had significantly less of a yellow tint. Unintentionally doped crystals are n-type but Hall effect data is not yet available.

Under our typical growth conditions GaN crystals typically have one larger and one smaller polar hexagonal facet, with one set of orthogonally-oriented facets and one set of pyramidal facets on one end (Fig. 3). We have determined the polarity of the crystals by single-crystal x-ray diffraction with Mo K α radiation up to $2\theta = 140^\circ$, or $\sin(\theta)/\lambda = 1.3 \text{ \AA}$, comparing the measured intensities of approximately 2000 reflections, averaged to 280 independent reflections, to those predicted using the known scattering cross sections of Ga and N. An excellent fit was achieved, with absolute structure (Flack) parameters of -0.10(8) and -0.03(7). The conclusion of the analysis is that the large hexagonal face is (0001) Ga. Similar and reverse polarities of prismatic GaN crystals grown in a Na/Ga alloy have been reported [12]. On the macro scale, the Ga surface is typically very smooth and the N surface somewhat rough.

The surface topography of some as-grown crystals was examined by Atomic Force Microscopy (AFM; Nanoscope III, tapping mode). A $5 \times 5 \text{ \mu m}$ scan of a Ga face is shown in Fig. 6. The RMS roughness was about 1.3 nm in these scans and was dominated by bumps, which may be residual particulates or precipitates produced during cooldown from growth conditions. The N face appeared similar in many regions of the surface, but micron-sized features were present elsewhere. A crystal was etched in 20% KOH at room temperature and re-examined by AFM. The Ga face was unchanged while the N face was etched, in agreement with previous reports [12] and confirming the polarity assignment.

The room-temperature photoluminescence spectrum, excited by a 2 ns nitrogen laser at 337 nm, was dominated by band-edge emission. Raman spectra were taken in back-scattering geometry with the beam either parallel or perpendicular to the c-axis of the crystal. The results are shown in Fig. 7. The mode assignments and frequencies of the observed peaks are: A_1 (TO) 530 cm^{-1} ; E_1 (TO) 558 cm^{-1} ; E_2 (high) 569 cm^{-1} ; A_1 (LO) 734 cm^{-1} ; and E_1 (LO) 742 cm^{-1} . The selection rules and frequencies all agree with the literature to within $1-2 \text{ cm}^{-1}$ [14]. Particularly noteworthy are the appearance of unshifted LO peaks and the absence of a broad peak assignable to phonon-plasmon coupling, which indicate no significant strain and a carrier concentration below about 10^{17} cm^{-3} [15].



cctm of GaN crystal in (-)-Z configurations.

in two ways. Many or most and may therefore be res no sample preparation. A fig. 8. Approximately 10^7 nents. By contrast, many 9).

defect-selective etching. We ing [17], which offers of the etch conditions. n etch pit density of 2×10^7 is on the HVPE seeds used in ay small, spontaneously crystals grown on HVPE seeds 10^8 cm^{-2} in the regions However, GaN material that of etch pits, as shown in the N was less than 500 cm^{-2} in



Fig. 10. Etched GaN crystal near boundary of underlying HVPE seed.

Spontaneously-nucleated and laterally-grown GaN crystals thus have state-of-the-art dislocation densities and are very high quality in all aspects except for a high impurity content, which is believed to be the source of the observed yellow color. We expect that purification of the polycrystalline GaN and mineralizer raw materials will greatly reduce the impurity levels. The scalability of crystal growth in supercritical fluids is well established, and we believe that continued development of the present method will permit low-cost manufacturing of high-quality true bulk GaN boules and wafers larger than 50 mm in diameter.

ACKNOWLEDGMENTS

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REFERENCES

1. T. Mukai and S. Nakamura, *Jpn. J. Appl. Phys.* **38**, 5735 (1999); T. Nishida, H. Saito, and N. Kobayashi, *Appl. Phys. Lett.* **79**, 711 (2001); A. Yasan, R. McClintock, K. Mayes, S. R. Darvish, H. Zhang, P. Kung, M. Ramezani, S. K. Lee, and J. Y. Han, *Appl. Phys. Lett.* **81**, 2151 (2002); S. Yu Karpov and Y. N. Mukarov, *Appl. Phys. Lett.* **81**, 4721 (2002).
2. S. Nakamura, *MRS Bulletin*, May 1998, 37; S. Nagahama, N. Iwasa, M. Senoh, T. Matsushita, Y. Sugimoto, H. Kiyoku, T. Kozaki, M. Sano, H. Matsumura, H. Umemoto, K. Chocho, and T. Mukai, *Jpn. J. Appl. Phys.* **39**, L647 (2000).
3. H. P. Maruska and J. J. Tietjen, *Appl. Phys. Lett.* **15**, 327 (1969); R. J. Molnar, in *Gallium Nitride II*, ed. J. I. Pankove and T. D. Moustakas, Semiconductors and Semimetals, Vol. 57 (Academic Press, San Diego, 1999).
4. K. Y. Lee and K. H. Auh, *Jpn. J. Appl. Phys.* **40**, L13 (2001); K. Motoki, T. Okanaka, N. Matsumoto, M. Matsushima, H. Kimura, H. Kasai, K. Takemoto, K. Uematsu, T. Hirano, M. Nakayama, S. Nakahata, M. Ueno, D. Hara, Y. Kumagai, A. Koukita, and H. Seki, *Jpn. J. Appl. Phys.* **40**, L140 (2001); R. P. Vaudo, X. Xu, C. Loria, A. D. Salant, J. S. Flynn, and G. R. Brandes, *Phys. Stat. Sol. (a)* **194**, 494 (2002).
5. S. Porowski, *MRS Internet J. Nitride Semicond. Res.* **4S1**, G1.3 (1999).
6. T. Inoue, Y. Seki, O. Oda, S. Kurai, Y. Yamada, and T. Taguchi, *Phys. Stat. Sol. (b)* **223**, 15 (2001); D. R. Gilbert, A. Novikov, N. Patrin, J. S. Budni, F. Kelly, R. Chodolka, R. Abbaschian, S. J. Pearton, and R. Singh, *Appl. Phys. Lett.* **77**, 4172 (2000).
7. M. Aoki, H. Yamane, M. Shimada, S. Sarayama, and F. J. DiSalvo, *Cryst. Growth Design* **1**, 119 (2001); V. Soukhovoev, V. Ivanov, Yu. Melnik, A. Davydov, D. Tsvetkov, K. Tsvetkova, I. Nikitina, A. Zubrilov, A. Lavrentiev, and V. Dmitriev, *Phys. Stat. Sol. (a)* **188**, 411 (2001); F. Kawamura, T. Iwahashi, K. Omae, M. Morishita, M. Yoshimura, Y. Mori, and T. Sasaki, *Jpn. J. Appl. Phys.* **42**, L4 (2003).
8. R. Dwiliński, R. Doradziński, J. Garczyński, L. Siczputowski, J. M. Baronowski, and M. Kamińska, *Diamond Relat. Mater.* **7**, 1348 (1998); D. R. Ketchum and J. W. Kolis, *J. Cryst. Growth* **222**, 431 (2001); A. P. Purdy, *Chem. Mater.* **11**, 1648 (1999); C. Collado, G.